

Zero Recovery Silicon Carbide Schottky Diode

PRODUCT APPLICATIONS

- Anti-Parallel Diode

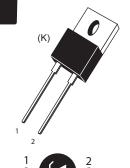
 Switchmode Power Supply
 Inverters
- Power Factor Correction (PFC)

PRODUCT FEATURES

- Zero Recovery Time (t_{rr})
- Popular TO-220 Package
- · Low Forward Voltage
- Low Leakage Current

PRODUCT BENEFITS

- Higher Reliability Systems
- Minimizes or eliminates snubber



- 1 Cathode
- 2 Anode Back of Case - Cathode

MAXIMUM RATINGS

 $T_C = 25^{\circ}C$ unless otherwise specified.

Symbol	Characteristic / Test Conditions		Ratings	Unit	
V _R	Maximum D.C. Reverse Voltage				
V _{RRM}	Maximum Peak Repetitive Reverse Voltage		650	Volts	
V _{RWM}	Maximum Working Peak Reverse Voltage				
	Maximum D.C. Forward Current	T _c = 25°C	17		
I _F		T _C = 100°C	9		
I _{FRM}	Repetitive Peak Forward Surge Current (T _J = 45°C, t _p = 10ms, Half Sine Wave)		50	Amps	
I _{FSM}	Non-Repetitive Forward Surge Current (T _J = 25°C, t _p = 10ms, Half Sine)		110		
Ртот	Power Dissipation	T _C = 25°C	63	10/	
		T _C = 110°C	20	W	
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to 150	- °C	
T _L	Lead Temperature for 10 Seconds		300		

STATIC ELECTRICAL CHARACTERISTICS

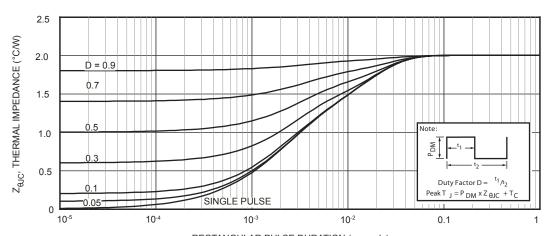
Symbol	Characteristic / Test Conditions		Min	Тур	Max	Unit
$V_{_{\rm F}}$	Forward Voltage	I _F = 10A T _J = 25°C		1.5	1.8	Volts
		I _F = 10A, T _J = 150°C		2.0		
I _{RM}	Maximum Reverse Leakage Current	V _R = 650V T _J = 25°C		10	200	μΑ
		V _R = 650V, T _J = 150°C		125		
Q _c	Total Capactive Charge $V_R = 300V$, $I_F = 10A$, di/dt = -500A/ μ s, $T_J = 25^{\circ}C$			80		nC
C _T	Junction Capacitance $V_R = 1V$, $T_J = 25^{\circ}C$, $f = 1MHz$			300		pF
	Junction Capacitance V _R = 100V, T _J = 25°C, f = 1MHz			72		
	Junction Capacitance $V_R = 300V$, $T_J = 25$ °C, $f = 1$ MHz			47		

THERMAL AND MECHANICAL CHARACTERISTICS

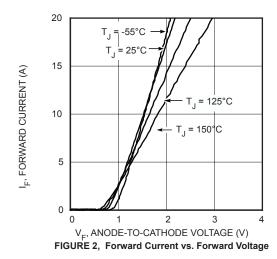
Symbol	Characteristic / Test Conditions	Min	Тур	Max	Unit
$R_{\theta JC}$	Junction-to-Case Thermal Resistance			2.0	°C/W
W _T	Package Weight		0.07		oz
			1.9		g
Torque	Maximum Mounting Torque			6.4	lb∙in
				0.7	N·m

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TYPICAL PERFORMANCE CURVES



RECTANGULAR PULSE DURATION (seconds)
FIGURE 1. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION



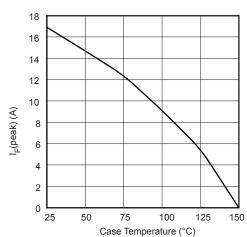
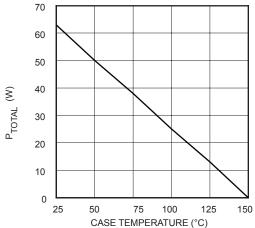
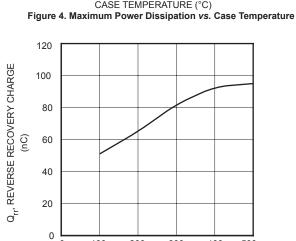


FIGURE 3, Maximum Forward Current vs. Case Temperature





200

 V_R , REVERSE VOLTAGE (V)

100

Figure 6. Reverse Recovery Charge vs. V_R

300

400

500

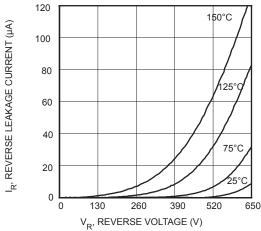
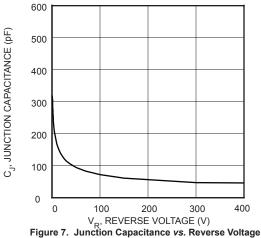
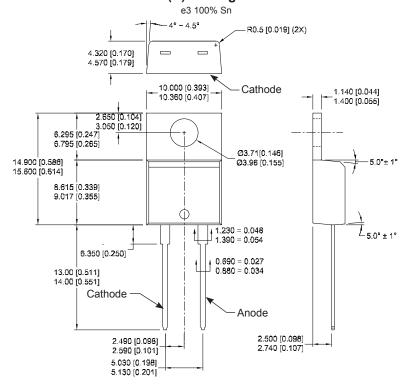


Figure 5. Reverse Leakage Currents vs. Reverse Voltage



TO-220 (K) Package Outline



Dimensions in millimeters and [inches]

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